

RJL5014DPP

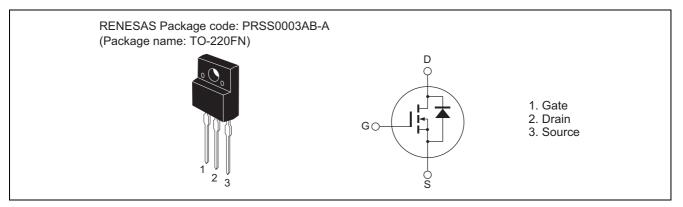
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1690-0300 Rev.3.00 Jun 13, 2008

Features

- Built-in fast recovery diode
- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	500	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	ID ^{Note4}	19	А
Drain peak current	Note1 D (pulse)	57	А
Body-drain diode reverse drain current	I _{DR}	19	А
Body-drain diode reverse drain peak current	Note1 I _{DR (pulse)}	57	А
Avalanche current	I _{AP} ^{Note3}	4	А
Avalanche energy	E _{AR} ^{Note3}	0.88	mJ
Channel dissipation	Pch Note2	35	W
Channel to case thermal impedance	θch-c	3.57	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

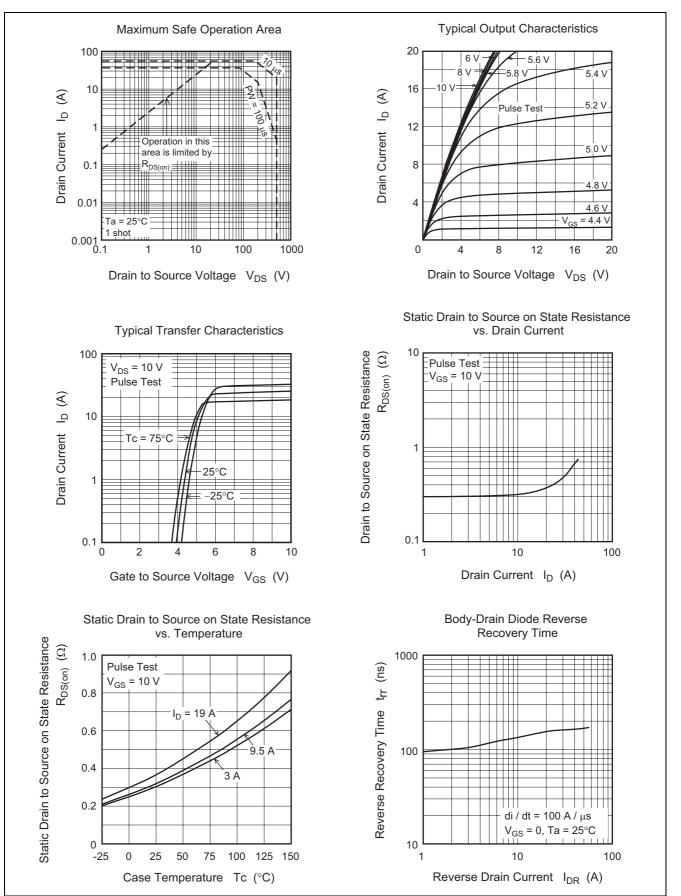
- 2. Value at Tc = 25° C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area

Electrical Characteristics

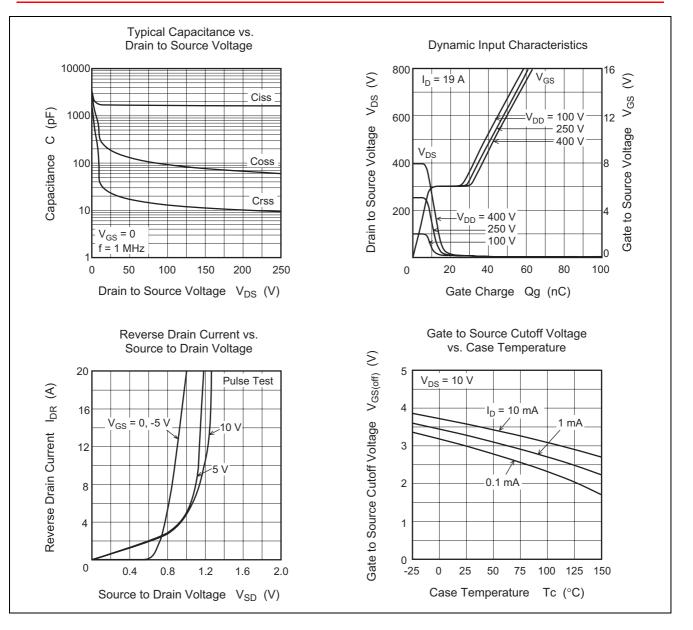
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	500	—	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	—	—	10	μΑ	$V_{DS} = 500 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I _{GSS}	_	—	±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
Gate to source cutoff voltage	V _{GS(off)}	2.0	—	4.0	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	0.32	0.40	Ω	$I_D = 9.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$
resistance						
Input capacitance	Ciss	_	1700	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	190		pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss		23		pF	
Turn-on delay time	t _{d(on)}	_	32		ns	I _D = 9.5 A
Rise time	tr	_	27	—	ns	$V_{GS} = 10 V$ $R_L = 26.3 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	t _{d(off)}	_	95	—	ns	
Fall time	t _f	_	20	—	ns	
Total gate charge	Qg	_	43	—	nC	V _{DD} = 400 V
Gate to source charge	Qgs	_	8.2	—	nC	V _{GS} = 10 V I _D = 19 A
Gate to drain charge	Qgd	_	21.8	_	nC	
Body-drain diode forward voltage	V _{DF}	_	1.00	1.65	V	$I_F = 19 \text{ A}, V_{GS} = 0^{\text{Note5}}$
Body-drain diode reverse recovery time	t _{rr}	_	160		ns	$I_F = 19 \text{ A}, V_{GS} = 0$
						di _F /dt = 100 A/µs

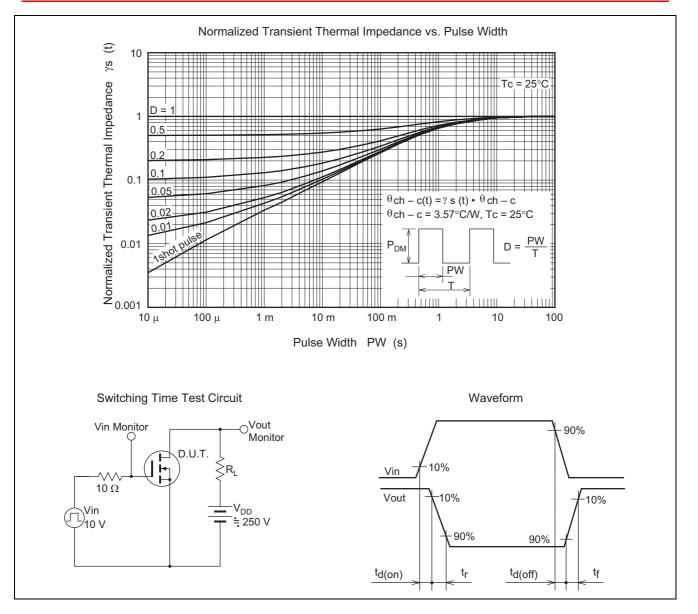
Notes: 5. Pulse test

Main Characteristics

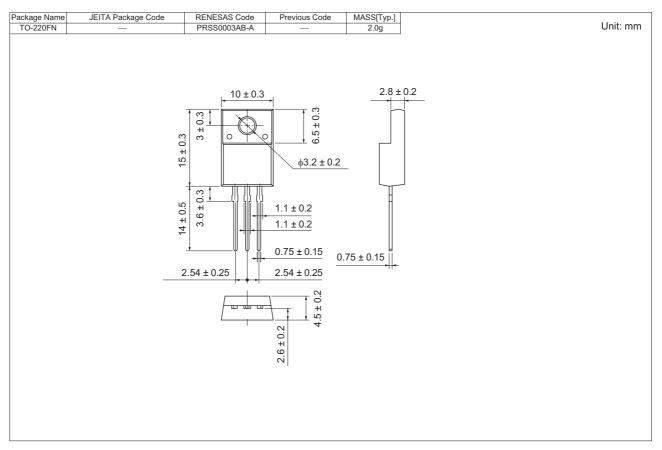


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Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJL5014DPP-00-T2	1050 pcs	Box (Tube)

RenesasTechnology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

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